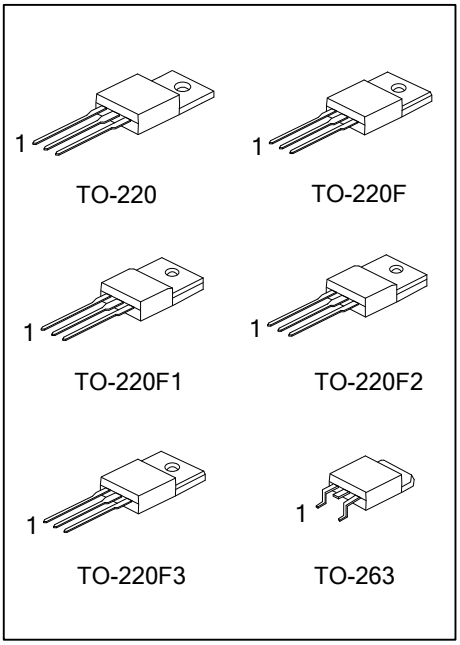
# 12N65K-MT

*Power MOSFET*

## 12A, 650V N-CHANNEL POWER MOSFET




### ■ DESCRIPTION

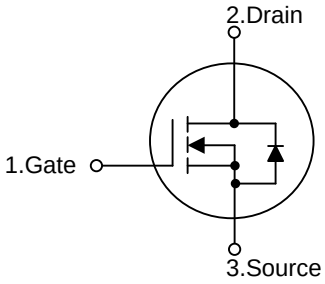
The UTC **12N65K-MT** are N-Channel enhancement mode power field effect transistors (MOSFET) which are produced by using UTC's proprietary, planar stripe and DMOS technology.

These devices are suited for high efficiency switch mode power supply. To minimize on-state resistance, provide superior switching performance and withstand high energy pulse in the avalanche and commutation mode, the advanced technology has been especially tailored.

### ■ FEATURES

* $R_{DS(ON)} \leq 0.7\Omega$ @ $V_{GS}$=10V, $I_D$=6.0A
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability, high ruggedness

### ■ SYMBOL




### ■ ORDERING INFORMATION

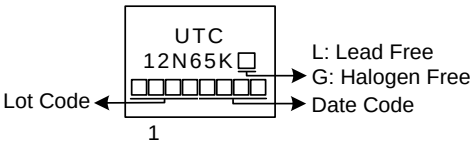
| Ordering Number | | Package | Pin Assignment | | | Packing |
|---|---|---|---|---|---|---|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 12N65KL-TA3-T | 12N65KG-TA3-T | TO-220 | G | D | S | Tube |
| 12N65KL-TF1-T | 12N65KG-TF1-T | TO-220F1 | G | D | S | Tube |
| 12N65KL-TF2-T | 12N65KG-TF2-T | TO-220F2 | G | D | S | Tube |
| 12N65KL-TF3-T | 12N65KG-TF3-T | TO-220F | G | D | S | Tube |
| 12N65KL-TF3T-T | 12N65KG-TF3T-T | TO-220F3 | G | D | S | Tube |
| 12N65KL-TQ2-T | 12N65KG-TQ2-T | TO-263 | G | D | S | Tube |
| 12N65KL-TQ2-R | 12N65KG-TQ2-R | TO-263 | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

12N65KG-TA3-T
(1)Packing Type
(2)Package Type
(3)Green Package

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2
TF3: TO-220F, TF3T: TO-220F3, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

## ■ MARKING



## ■ ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 650 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±30 | V |
| Drain Current | Continuous | $I_D$ | 12 | A |
| | Pulsed (Note 2) | $I_{DM}$ | 48 | A |
| Avalanche Energy | Single Pulsed (Note 3) | $E_{AS}$ | 400 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 2.7 | V/ns |
| Power Dissipation | TO-220/TO-263 | $P_D$ | 225 | W |
| | TO-220F/TO-220F1/ TO-220F2/TO-220F3 | | 51 | W |
| Junction Temperature | | $T_J$ | +150 | °C |
| Operating Temperature | | $T_{OPR}$ | -55 ~ +150 | °C |
| Storage Temperature | | $T_{STG}$ | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature
3. L =5.55mH, $I_{AS}$ = 12A, $V_{DD}$ = 50V, $R_G$ = 25Ω, Starting $T_J$ = 25°C
4. $I_{SD}$ ≤ 12A, di/dt ≤200A/μs, $V_{DD}$ ≤$BV_{DSS}$ Starting $T_J$ = 25°C

## ■ THERMAL DATA

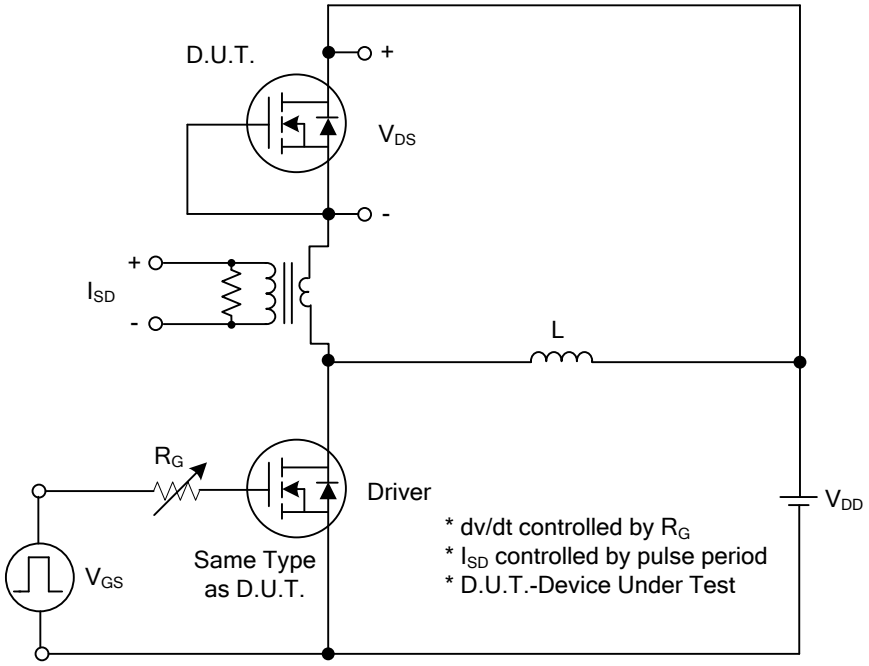
| PARAMETER | | SYMBOL | RATING | UNIT |
|---|---|---|---|---|
| Junction to Ambient | | $\theta_{JA}$ | 62.5 | °C/W |
| Junction to Case | TO-220/TO-263 | $\theta_{JC}$ | 0.56 | °C/W |
| | TO-220F/TO-220F1/ TO-220F2/TO-220F3 | | 2.43 | °C/W |

## ■ ELECTRICAL CHARACTERISTICS ($T_J$=25°C, unless otherwise specified)

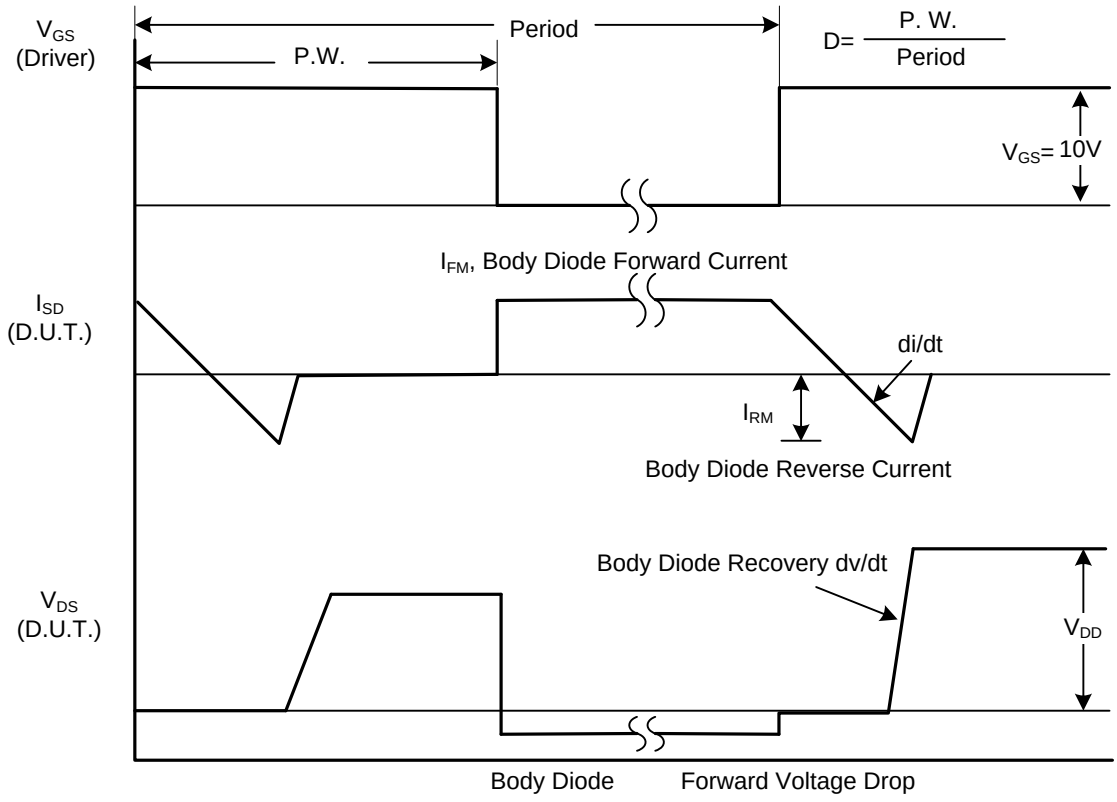
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V, $I_D$=250μA | 650 | | | V |
| Drain-Source Leakage Current | $I_{DSS}$ | $V_{DS}$=650V, $V_{GS}$=0V | | | 10 | μA |
| Gate-Source Leakage Current | $I_{GSS}$ | $V_{GS}$=±30V, $V_{DS}$=0V | | | ±100 | nA |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\triangle T_J$ | $I_D$=250μA, Referencedto25°C | | 0.7 | | V/°C |
| **ON CHARACTERISTICS** | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{DS}$=$V_{GS}$, $I_D$=250μA | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=6.0A | | 0.60 | 0.7 | Ω |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{DS}$=25V, $V_{GS}$=0V, f=1MHz | | 2126 | | pF |
| Output Capacitance | $C_{OSS}$ | | | 170 | | pF |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | 5 | | pF |
| **SWITCHING CHARACTERISTICS** | | | | | | |
| Total Gate Charge | $Q_G$ | $V_{DS}$=100V, $V_{GS}$=10V, $I_D$=12A, $I_G$=1mA (Note1,2) | | 53 | | nC |
| Gate-Source Charge | $Q_{GS}$ | | | 10 | | nC |
| Gate-Drain Charge | $Q_{GD}$ | | | 7 | | nC |
| Turn-On Delay Time | $t_{D(ON)}$ | $V_{DD}$=100V, $V_{GS}$=10V, $I_D$=12A $R_G$=25Ω (Note1,2) | | 26 | | ns |
| Turn-On Rise Time | $t_R$ | | | 18 | | ns |
| Turn-Off Delay Time | $t_{D(OFF)}$ | | | 130 | | ns |
| Turn-Off Fall Time | $t_F$ | | | 31 | | ns |
| **SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS** | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | $I_S$ | | | | 12 | A |
| Maximum Pulsed Drain-Source Diode Forward Current | $I_{SM}$ | | | | 48 | A |
| Drain-Source Diode Forward Voltage | $V_{SD}$ | $I_S$=12A, $V_{GS}$=0V | | | 1.4 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_S$=12A, $V_{GS}$=0V di/dt=100A/μs(Note1) | | 415 | | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | | 5.5 | | μC |

Notes: 1. Pulse Test : Pulse width ≤300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

## ■ TEST CIRCUITS AND WAVEFORMS

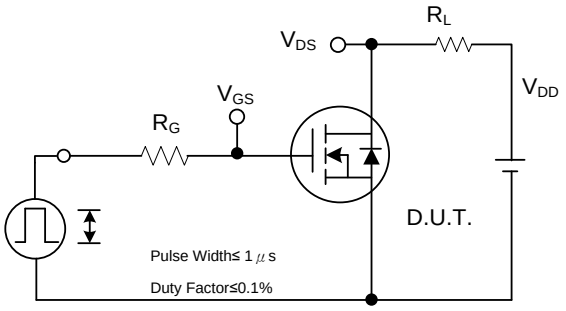



**Peak Diode Recovery dv/dt Test Circuit**

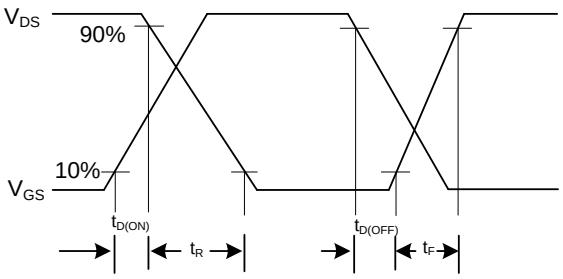



**Peak Diode Recovery dv/dt Waveforms**

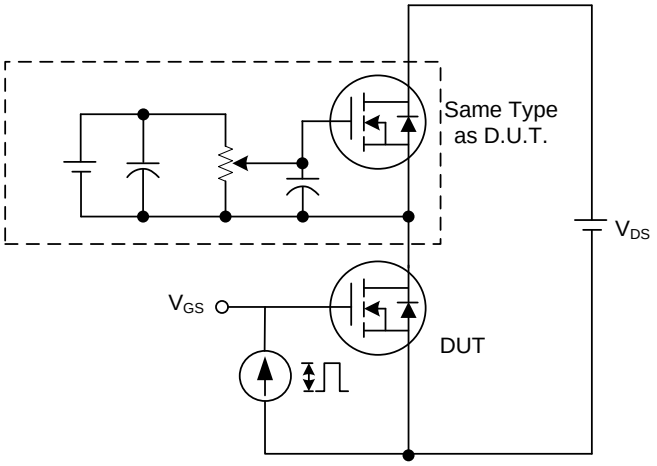
## ■ TEST CIRCUITS AND WAVEFORMS



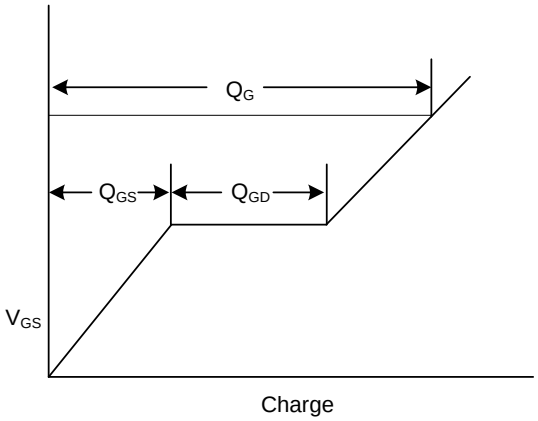

**Switching Test Circuit**



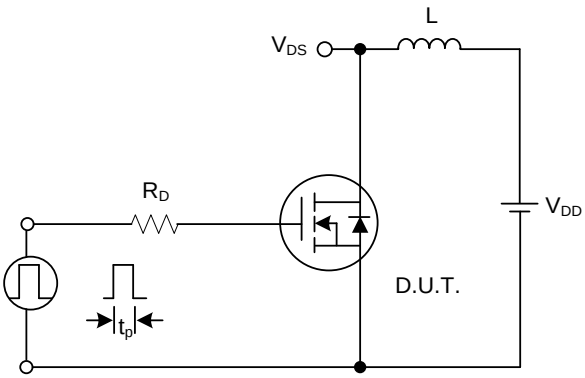

**Switching Waveforms**



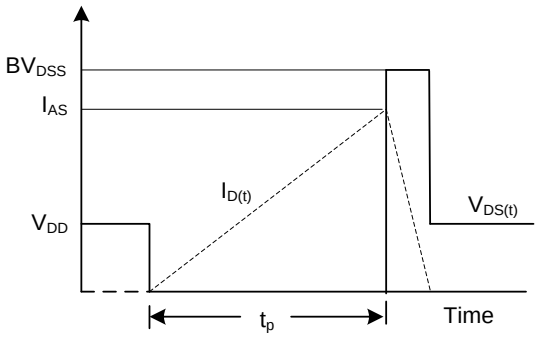

**Gate Charge Test Circuit**




**Gate Charge Waveform**



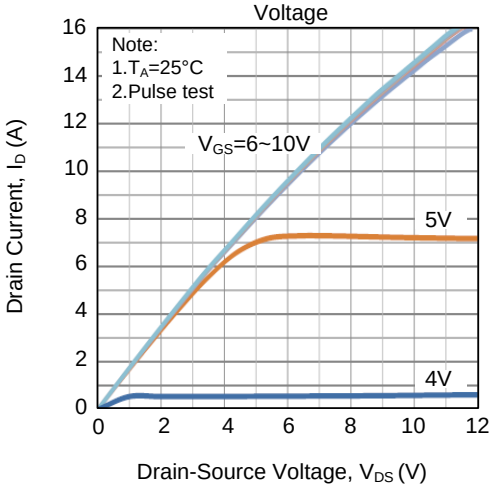

**Unclamped Inductive Switching Test Circuit**



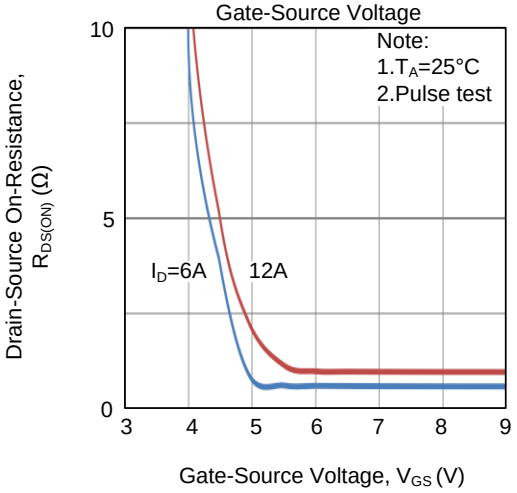

**Unclamped Inductive Switching Waveforms**

## ■ TYPICAL CHARACTERISTICS

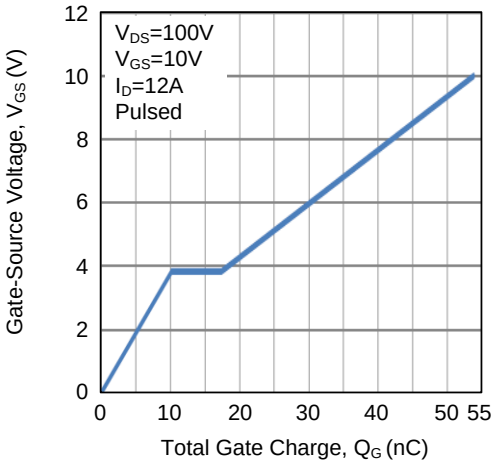
Drain Current vs. Drain-Source Voltage



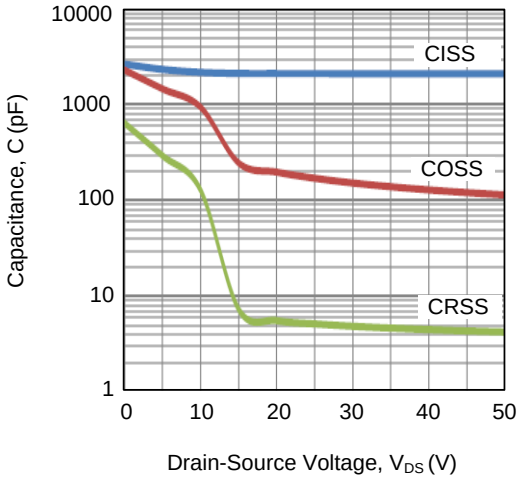

Drain-Source On-Resistance vs. Gate-Source Voltage



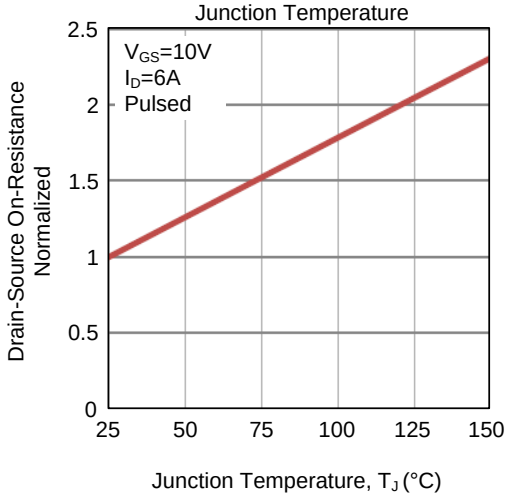

Gate Charge Characteristics



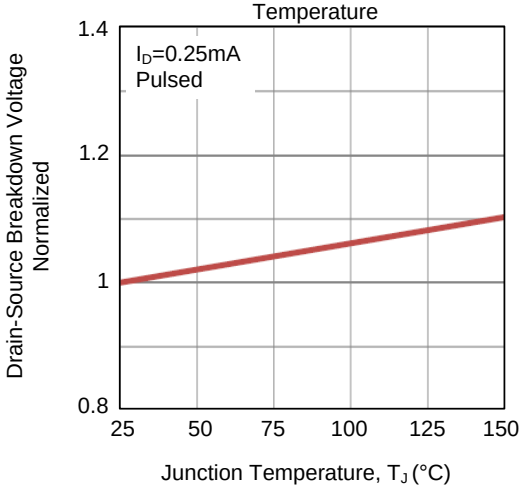

Capacitance Characteristics




Drain-Source On-Resistance vs. Junction Temperature

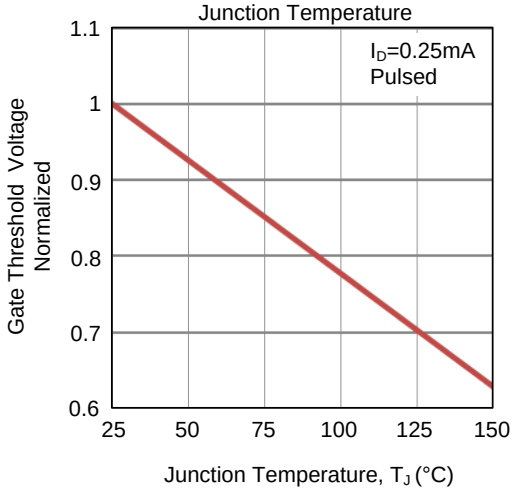



Breakdown Voltage vs. Junction Temperature

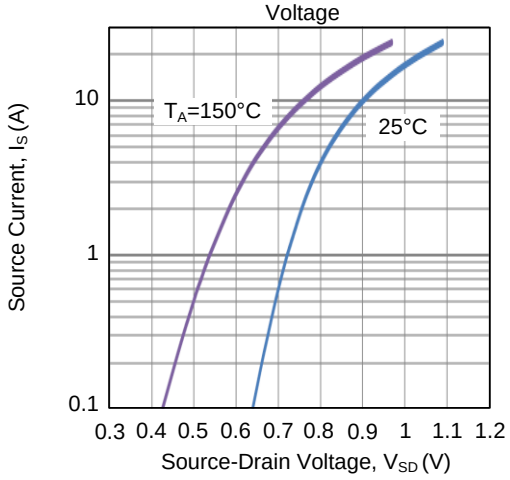


## ■ TYPICAL CHARACTERISTICS (Cont.)

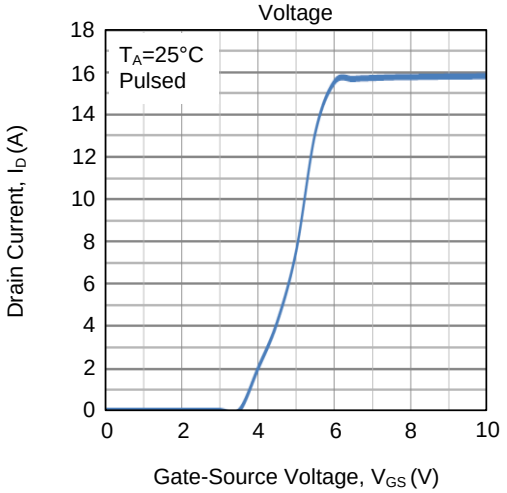
Gate Threshold Voltage vs. Junction Temperature



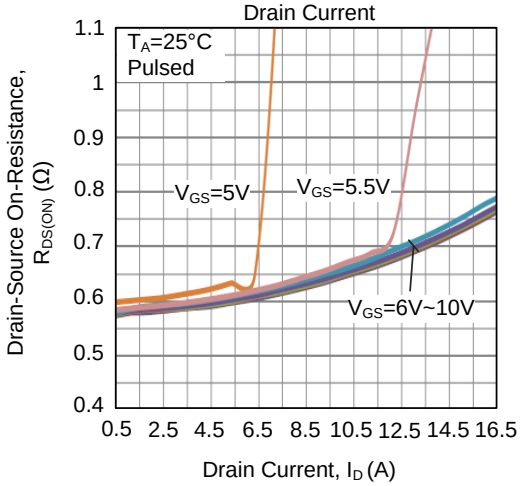

Source Current vs. Source-Drain Voltage



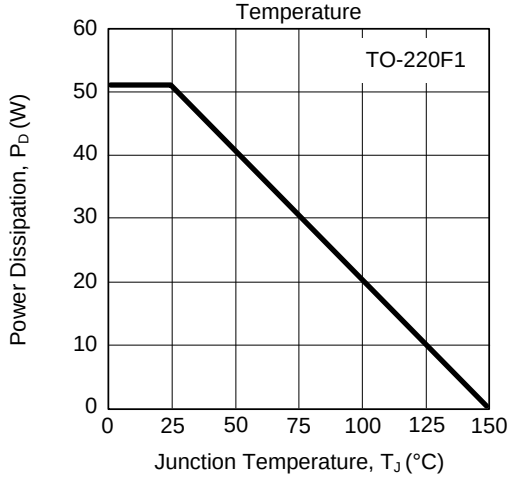

Drain Current vs. Gate-Source Voltage



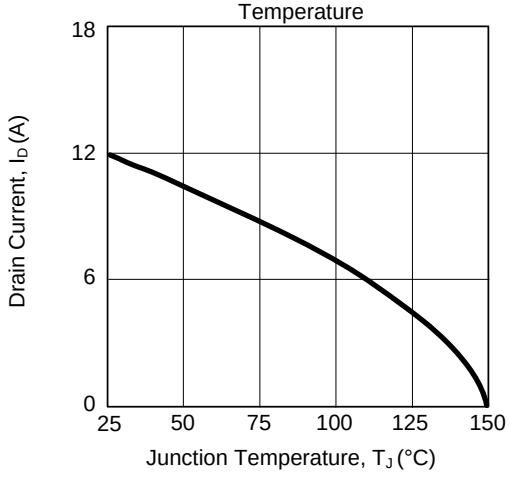

Drain-Source On-Resistance vs. Drain Current




Power Dissipation vs. Junction Temperature




Drain Current vs. Junction Temperature



## ■ TYPICAL CHARACTERISTICS (Cont.)